

BD810

Silicon PNP Transistors



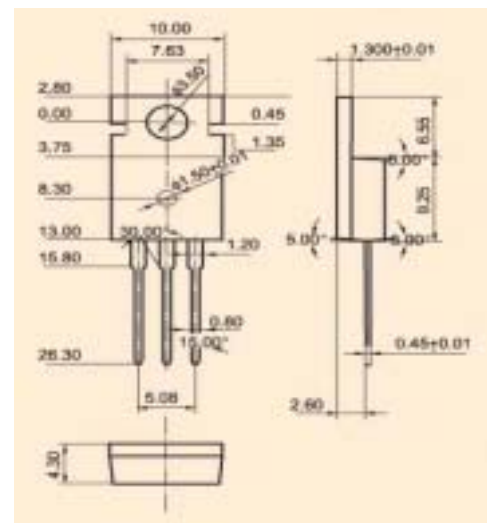
B C E

◆ Features

- . Designed for use in high power audio amplifiers utilizing complementary or quasi complementary circuits.
- . With TO-220 package

◆ Absolute Maximum Ratings Tc=25°C

SYMBOL	PARAMETER	RATING	UNIT
V _{CB0}	Collector to base voltage	80	V
V _{CEO}	Collector to emitter voltage	80	V
V _{EBO}	Emitter to base voltage	5.0	V
I _B	Base collector current	6.0	A
I _C	Collector current	10	A
P _C	Collector power dissipation	90	W
T _j	Junction temperature	150	°C
T _{stg}	Storage temperature	-55~150	°C



TO-220

◆ Electrical Characteristics Tc=25°C

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
I _{CB0}	Collector-base cut-off current	V _{CB} =80V; I _E =0			1.0	mA
I _{EBO}	Emitter-base cut-off current	V _{EB} =5.0V; I _C =0			2.0	mA
I _{CEO}	Collector-emitter cut-off current					
V _{CB0}	Collector-base breakdown voltage					
V _{(BR)ceo}	Collector-emitter breakdown voltage	I _C =0.1A; I _B =0	80			V
V _{EBO}	Emitter-base breakdown voltage					
V _{CE(sat-1)}	Collector-emitter saturation voltages	I _C =3A; I _B =0.3A			1.1	V
V _{CE(sat-2)}	Collector-emitter saturation voltages					
h _{FE-1}	Forward current transfer ratio	I _C =2A; V _{CE} =2V	30			
h _{FE-2}	Forward current transfer ratio	I _C =4A; V _{CE} =2V	15			
h _{FE-3}	Forward current transfer ratio					
V _{BE(on)1}	Base-emitter on voltages	I _C =4A; V _{CE} =2V			1.6	V
V _{BE(on)2}	Base-emitter on voltages					
f _T	Transition frequency	V _{CE} =10V ; I _C =1A; f=1MHz	1.5			MHz
C _{ob}	Output Capacitance					